

CY7C1041CV33

4-Mbit (256K x 16) Static RAM

Features

- Temperature ranges
 - □ Commercial: 0°C to 70°C
 - Industrial: –40°C to 85°C
 - □ Automotive-A: -40°C to 85°C
 - □ Automotive-E: -40°C to 125°C
- Pin and function compatible with CY7C1041BV33
- High speed
 - □ t_{AA} = 10 ns (Commercial, Industrial and Automotive-A) □ t_{AA} = 12 ns (Automotive-E)
- Low active power 324 mW (max)
- 2.0V data retention
- Automatic power down when deselected
- TTL-compatible inputs and outputs
- **Easy** memory expansion with \overline{CE} and \overline{OE} features
- Available in Pb-free and non Pb-free 44-pin 400 Mil SOJ, 44-pin TSOP II and 48-Ball FBGA packages

Functional Description

The CY7C1041CV33 is a high performance CMOS static RAM organized as 262,144 words by 16 bits.

To write to the device, take Chip Enable $\overline{(CE)}$ and Write Enable $\overline{(WE)}$ inputs LOW. If Byte Low Enable (BLE) is LOW, then data from IO pins (IO₀ through IO₇), is written into the location specified on the address pins (A₀ through A₁₇). If Byte High Enable (BHE) is LOW, then data from IO pins (IO₈ through IO₁₅) is written into the location specified on the address pins (A₀ through A₁₇).

To read <u>from</u> the device, take Chip Enable ($\overline{\text{CE}}$) and Output Enable ($\overline{\text{OE}}$) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins appear on IO₀ to IO₇. If Byte High Enable (BHE) is LOW, then data from memory appears on IO₈ to IO₁₅. For more information, see the Truth Table on page 9 for a complete description of Read and Write modes.

The input and output pins (IO_0 through IO_{15}) are placed in a high impedance state when the device is deselected (CE HIGH), the outputs are disabled (OE HIGH), the BHE and BLE are disabled (BHE, BLE HIGH), or during a write operation (CE LOW and WE LOW).

For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines.



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Selection Guide

Description		-10	-12	-15	-20	Unit
Maximum Access Time	10	12	15	20	ns	
Maximum Operating Current	Commercial	90	85	80	75	mA
	Industrial	100	95	90	85	mA
	Automotive-A	100			85	mA
	Automotive-E		120		90	mA
Maximum CMOS Standby Current	Commercial/ Industrial	10	10	10	10	mA
	Automotive-A	10			10	mA
	Automotive-E		15		15	mA

Pin Configuration

Figure 1. 44-Pin SOJ/TSOP II (Top View) ^[1]

$A_0 \square 1$	44 🗖 A ₁₇
$A_1 \square 2$	43 🗖 A ₁₆
A ₂ <u> </u>	42 🗆 A ₁₅
A ₃ <u>□</u> 4	41 🗆 OE
A ₄ _ 5	40 🗆 BHE
CE C 6	39 🗌 BLE
IO ₀	38 🗖 IO ₁₅
IO ₁	37 🛛 IO ₁₄
IO ₂	36 🛛 IO ₁₃
IO ₃ <u>□</u> 10	35 🛛 IO ₁₂
	34 🗆 V _{SS}
	33 🗖 V _{CC}
	32 🗌 IO ₁₁
	31 IO ₁₀
	30 🗌 10 ₉
	29 10 ₈
WE □ 17 A ₅ □ 18	
A	$27 \square A_{14}$
A ₆ □ 19 A ₇ □ 20	26 □ A ₁₃ 25 □ A ₁₂
A ₈ □ 21	25 □ A ₁₂ 24 □ A ₁₁
$A_9 \square 22$	
· ·9 –	23 🗆 A ₁₀

Figure 2. 48-Ball FBGA Pinout (Top View) ^[1]



Note
1. NC pins are not connected on the die.



Pin Definitions

Pin Name	SOJ, TSOP Pin Number	BGA Pin Number	Ю Туре	Description			
A ₀ -A ₁₇	1–5, 18–27, 42–44	A3, A4, A5, B3, B4, C3, C4, D4, H2, H3, H4, H5, G3, G4, F3, F4, E4, D3	Input	Address Inputs. Used to select one of the address locations.			
10 ₀ -10 ₁₅	7–10,13–16, 29–32, 35–38	B1, C1, C2, D2, E2, F2, F1, G1, B6, C6, C5, D5, E5, F5, F6, G6	Input or Output	ut Bidirectional Data IO lines . Used as input or output lines depend on operation.			
NC	28	A6, E3, G2, H1, H6	No Connect	No Connects. Not connected to the die.			
WE	17	G5	Input or Control	Write Enable Input, Active LOW. When selected LOW, a write is conducted. When deselected HIGH, a read is conducted.			
CE	6	B5	Input or Control	Chip Enable Input, Active LOW. When LOW, selects the chip. When HIGH, deselects the chip.			
BHE, BLE	40, 39	B2, A1	Input or Control				
ŌĒ	41	A2	Input or Control	Output Enable, Active LOW . Controls the direction of the IO pins. When LOW, the IO pins are allowed to behave as outputs. When deasserted HIGH, the IO pins are tri-stated and act as input data pins.			
V _{SS}	12, 34	D1, E6	Ground	Ground for the Device. Connected to ground of the system.			
V _{CC}	11, 33	D6, E1	Power Supply	Power Supply Inputs to the Device.			



Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature65°C to +150°C
Ambient Temperature with Power Applied55°C to +125°C
Supply Voltage on V_{CC} Relative to $GND^{[2]}0.5V$ to +4.6V
DC Voltage Applied to Outputs in High Z State $^{[2]}$ 0.5V to $V_{CC}\text{+}0.5\text{V}$
DC Input Voltage ^[2] 0.5V to V _{CC} +0.5V
Current into Outputs (LOW) 20 mA

Static Discharge Voltage	>2001V
(MIL-STD-883, Method 3015)	

Latch Up Current>200 mA

Operating Range

Range	Ambient Temperature (T _A)	V _{cc}
Commercial	0°C to +70°C	3.3V ± 10%
Industrial	–40°C to +85°C	
Automotive-A	–40°C to +85°C	
Automotive -E	-40°C to +125°C	

Electrical Characteristics

Over the Operating Range

Parameter	Description	tions	-1	-10		2	-15		-20		Unit	
Parameter	Description	Test Condi	Min	Max	Min	Max	Min	Max	Min	Max	Unit	
V _{OH}	Output HIGH Voltage	$V_{CC} = Min, I_{OH} = -4$	l.0 mA	2.4		2.4		2.4		2.4		V
V _{OL}	Output LOW Voltage	$V_{CC} = Min, I_{OL} = 8.0$) mA		0.4		0.4		0.4		0.4	V
V _{IH}	Input HIGH Voltage			2.0	V _{CC} + 0.3	V						
V _{IL} ^[2]	Input LOW Voltage			-0.3	0.8	-0.3	0.8	-0.3	0.8	-0.3	0.8	V
I _{IX}	Input Leakage	$GND \leq V_I \leq V_{CC}$	Com'l/Ind'l	-1	+1	-1	+1	-1	+1	-1	+1	μA
	Current		Auto-A	-1	+1					-1	+1	
			Auto-E			-20	+20			-20	+20	
I _{OZ}	Output Leakage	$GND \leq V_{OUT} \leq V_{CC}$,	Com'l/Ind'l	-1	+1	-1	+1	-1	+1	-1	+1	μA
	Current	Output disabled	Auto-A	-1	+1					-1	+1	
			Auto-E			-20	+20			-20	+20	
I _{CC}	V _{CC} Operating	V _{CC} = Max,	Com'l		90		85		80		75	mA
	Supply Current	$f = f_{MAX} = 1/t_{RC}$	Ind'l		100		95		90		85	
			Auto-A		100						85	
			Auto-E				120				90	
I _{SB1}	Automatic CE Power	<u>Ma</u> x V _{CC} ,	Com'l/Ind'l		40		40		40		40	mA
	Down Current — TTL	$CE \ge V_{H}$	Auto-A		40						40	
	Inputs	$V_{IN} \ge V_{IH} \text{ or}$ $V_{IN} \le V_{IL}, f = f_{MAX}$	Auto-E				45				45	
I _{SB2}	Automatic CE Power	<u>Ma</u> x V _{CC} ,	Com'l/Ind'l		10		10		10		10	mA
	Down Current — CMOS Inputs	$CE \ge V_{CC} - 0.3V$,	Auto-A		10						10	
		$V_{IN} \ge V_{CC} - 0.3V$, or $V_{IN} \le 0.3V$, f = 0	Auto-E				15				15	

Note 2. V_{IL} (min) = -2.0V and V_{IH} (max) = V_{CC} + 0.5V for pulse durations of less than 20 ns.



Capacitance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Description Test Conditions					
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C$, f = 1 MHz, $V_{CC} = 3.3V$	8	pF			
C _{OUT}	Output Capacitance		8	pF			

Thermal Resistance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	SOJ	TSOP II	FBGA	Unit
Θ_{JA}	· /	Test conditions follow standard test methods and procedures for measuring	25.99	42.96	38.15	°C/W
Θ _{JC}	Thermal Resistance (Junction to Case)	thermal impedance, per EIA/JESD51	18.8	10.75	9.15	°C/W

AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms ^[3]







High-Z characteristics:



Note

3. AC characteristics (except High-Z) for 10-ns parts are tested using the load conditions shown in Figure (a). All other speeds are tested using the Thevenin load shown in Figure (b). High-Z characteristics are tested for all speeds using the test load shown in Figure (d).



Switching Characteristics

Over the Operating Range [4]

Devenueter	Deserie	Description			-12		-15		-20		Unit
Parameter	Description		Min	Max	Min	Max	Min	Max	Min	Max	Unit
Read Cycle	·		•	•	•				•		
t _{power} ^[5]	V _{CC} (Typical) to the First Ad	ccess	100		100		100		100		μS
t _{RC}	Read Cycle Time		10		12		15		20		ns
t _{AA}	Address to Data Valid			10		12		15		20	ns
t _{OHA}	Data Hold from Address C	hange	3		3		3		3		ns
t _{ACE}	CE LOW to Data Valid			10		12		15		20	ns
t _{DOE}	OE LOW to Data Valid	Comm'l/Ind'l/Auto-A		5		6		7		8	ns
		Auto-E				7				8	
t _{LZOE}	OE LOW to Low Z ^[6]		0		0		0		0		ns
t _{HZOE}	OE HIGH to High Z ^[6, 7]			5		6		7		8	ns
t _{LZCE}	CE LOW to Low Z ^[6]		3		3		3		3		ns
t _{HZCE}	CE HIGH to High Z ^[6, 7]			5		6		7		8	ns
t _{PU}	CE LOW to Power Up		0		0		0		0		ns
t _{PD}	CE HIGH to Power Down			10		12		15		20	ns
t _{DBE}	Byte Enable to Data Valid	Comm'l/Ind'l/Auto-A		5		6		7		8	ns
		Auto-E				7				8	
t _{LZBE}	Byte Enable to Low Z		0		0		0		0		ns
t _{HZBE}	Byte Disable to High Z			6		6		7		8	ns
Write Cycle ^{[8,}	, 9]										
t _{WC}	Write Cycle Time		10		12		15		20		ns
t _{SCE}	CE LOW to Write End		7		8		10		10		ns
t _{AW}	Address Setup to Write En	d	7		8		10		10		ns
t _{HA}	Address Hold from Write E	nd	0		0		0		0		ns
t _{SA}	Address Setup to Write Sta	art	0		0		0		0		ns
t _{PWE}	WE Pulse Width		7		8		10		10		ns
t _{SD}	Data Setup to Write End				6		7		8		ns
t _{HD}	Data Hold from Write End				0		0		0		ns
t _{LZWE}	WE HIGH to Low Z ^[6]				3		3		3		ns
t _{HZWE}	WE LOW to High Z ^[6, 7]			5		6		7		8	ns
t _{BW}	Byte Enable to End of Writ	e	7		8		10		10		ns

Notes

Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, and input pulse levels of 0 to 3.0V. t_{POWER} gives the minimum amount of time that the power supply is at typical V_{CC} values until the first memory access is performed. 4.

5.

The internal write time of the memory is defined by the overlap of \overline{CE} LOW, \overline{WE} LOW, and $\overline{BHE/BLE}$ LOW. \overline{CE} , \overline{WE} , and $\overline{BHE/BLE}$ must be LOW to initiate a write. The minimum Write cycle time for Write Cycle No. 3 (WE controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{HZWE} for Write Cycle No. 3 (WE controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{HZWE} for Write Cycle No. 3 (WE controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{HZWE} for Write Cycle No. 3 (WE controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{HZWE} for Write Cycle No. 3 (WE controlled, \overline{OE} LOW) is the sum of t_{HZWE} and t_{SD} . 6. 7.

8.

9.



Switching Waveforms









Notes

- 10. Device is continuously selected. \overline{OE} , \overline{CE} , \overline{BHE} , and/or $\overline{BLE} = V_{IL}$. 11. WE is HIGH for read cycle.

^{12.} Address valid prior to or coincident with \overline{CE} transition LOW.



Switching Waveforms (continued)



Figure 6. Write Cycle No. 1 (CE Controlled)^[13, 14]

Figure 7. Write Cycle No. 2 (BLE or BHE Controlled)



Notes 13. Data IO is high impedance if \overline{OE} , \overline{BHE} , and/or $\overline{BLE} = V_{IH}$. 14. If \overline{CE} goes HIGH simultaneously with WE going HIGH, the output remains in a high impedance state.



Switching Waveforms (continued)



Figure 8. Write Cycle No. 3 (WE Controlled, OE LOW)

Truth Table

CE	OE	WE	BLE	BHE	10 ₀ -10 ₇	10 ₈ – 10 ₁₅	Mode	Power
Н	Х	Х	Х	Х	High Z	High Z	Power Down	Standby (I _{SB})
L	L	Н	L	L	Data Out	Data Out	Read – All Bits	Active (I _{CC})
			L	Н	Data Out	High Z	Read – Lower Bits Only	Active (I _{CC})
			Н	L	High Z	Data Out	Read – Upper Bits Only	Active (I _{CC})
L	Х	L	L	L	Data In	Data In	Write – All Bits	Active (I _{CC})
			L	Н	Data In	High Z	Write – Lower Bits Only	Active (I _{CC})
			Н	L	High Z	Data In	Write – Upper Bits Only	Active (I _{CC})
L	Н	Н	Х	Х	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})
L	Х	Х	Н	Н	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})



Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
10			48-ball Fine Pitch BGA (Pb-Free)	Commercial
	CY7C1041CV33-10VC	51-85082	44-pin (400-mil) Molded SOJ	
	CY7C1041CV33-10VXC		44-pin (400-mil) Molded SOJ (Pb-Free)	
	CY7C1041CV33-10ZXC	51-85087	44-pin TSOP II (Pb-Free)	
	CY7C1041CV33-10BAI	51-85106	48-ball Fine Pitch BGA	Industrial
	CY7C1041CV33-10BAXI		48-ball Fine Pitch BGA (Pb-Free)	
	CY7C1041CV33-10ZI	51-85087	44-pin TSOP II	
	CY7C1041CV33-10ZXI		44-pin TSOP II (Pb-Free)	
	CY7C1041CV33-10BAXA	51-85106	48-ball Fine Pitch BGA (Pb-Free)	Automotive-A
	CY7C1041CV33-10ZSXA	51-85087	44-pin TSOP II (Pb-Free)	
12	CY7C1041CV33-12VXC	51-85082	44-pin (400-mil) Molded SOJ (Pb-Free)	Commercial
	CY7C1041CV33-12ZXC	51-85087	44-pin TSOP II (Pb-Free)	
	CY7C1041CV33-12ZI	51-85087	44-pin TSOP II	Industrial
	CY7C1041CV33-12ZXI		44-pin TSOP II (Pb-Free)	
	CY7C1041CV33-12BAXE	51-85106	48-ball Fine Pitch BGA (Pb-Free)	Automotive-E
	CY7C1041CV33-12ZSXE	51-85087	44-pin TSOP II (Pb-Free)	
15	CY7C1041CV33-15ZXC	51-85087	44-pin TSOP II (Pb-Free)	Commercial
	CY7C1041CV33-15VI	51-85082	44-pin (400-mil) Molded SOJ	Industrial
	CY7C1041CV33-15VXI		44-pin (400-mil) Molded SOJ (Pb-Free)	
	CY7C1041CV33-15ZI	51-85087	44-pin TSOP II	
	CY7C1041CV33-15ZXI		44-pin TSOP II (Pb-Free)	
20	CY7C1041CV33-20ZC	51-85087	44-pin TSOP II	Commercial
	CY7C1041CV33-20ZSXA	51-85087	44-pin TSOP II (Pb-Free)	Automotive-A
	CY7C1041CV33-20VE	51-85082	44-pin (400-mil) Molded SOJ	Automotive-E
	CY7C1041CV33-20VXE	1	44-pin (400-mil) Molded SOJ (Pb-Free)	
	CY7C1041CV33-20ZE	51-85087	44-pin TSOP II	
	CY7C1041CV33-20ZSXE	1	44-pin TSOP II (Pb-Free)	

Please contact your local Cypress sales representative for availability of these parts



Package Diagrams

Figure 9. 44-Pin (400 Mil) Molded SOJ, 51-85082





DIMENSION IN MM (INCH)

Package Diagrams (continued)

Figure 10. 44-Pin Thin Small Outline Package Type II, 51-85087





Package Diagrams (continued)









51-85106-*E



Document History Page

Document Title: CY7C1041CV33, 4-Mbit (256K x 16) Static RAM Document Number: 38-05134				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	109513	12/13/01	HGK	New Data Sheet
*A	112440	12/20/01	BSS	Updated 51-85106 from revision *A to *C
*В	112859	03/25/02	DFP	Added CY7C1042CV33 in BGA package Removed 1042 BGA option pin ACC Final Data Sheet
*C	116477	09/16/02	CEA	Add applications foot note to data sheet
*D	119797	10/21/02	DFP	Added 20-ns speed bin
*E	262949	See ECN	RKF	 Added Lead (Pb)-Free parts in the Ordering info (Page #9) Added Automotive Specs to Datasheet
*F	361795	See ECN	SYT	Added Pb-Free offerings in the Ordering Information
*G	435387	See ECN	NXR	Removed -8 Speed bin from Product offering. Corrected typo in description for BHE/BLE in pin definitions table on Page# 3 corrected their Pin name from OE2 to OE. Included the Maximum Ratings for Static Discharge Voltage and Latch up Current. Changed the description of I _{IX} current from Input Load Current to Input Leakage Current Added note# 4 on page# 4 Updated the Ordering Information table
*H	499153	See ECN	NXR	Added Automotive-A Operating Range Changed t_{power} value from 1 μ s to 100 μ s Updated Ordering Information table
*	2104110	See ECN	VKN/AESA	Added Automotive-E specs for 12 ns speed Updated Ordering Information table

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